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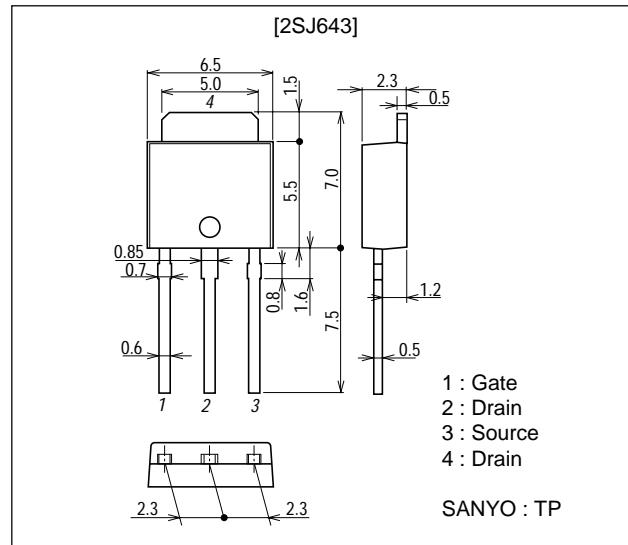
Ultrahigh-Speed Switching Applications

Features

- Low ON-resistance.
- 1.8V drive.

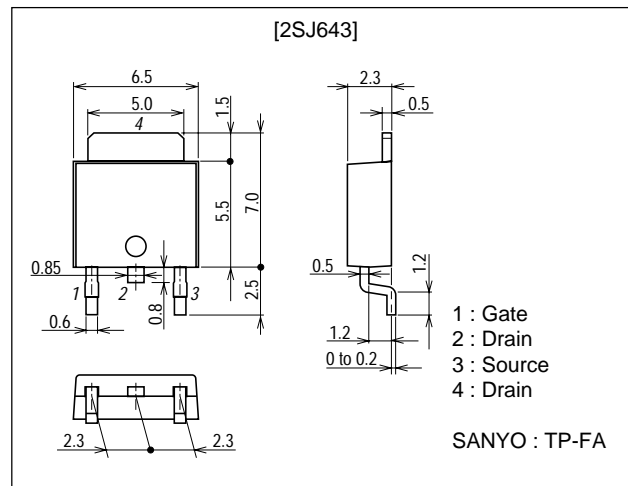
Package Dimensions

unit : mm
2083B



Package Dimensions

unit : mm
2092B



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SANYO Electric Co.,Ltd. Semiconductor Company

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

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Specifications

Absolute Maximum Ratings at Ta=25°C

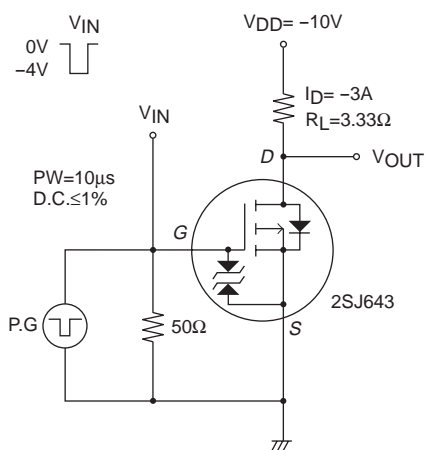
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-24	A
Allowable Power Dissipation	P _D		1	W
		T _c =25°C	10	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

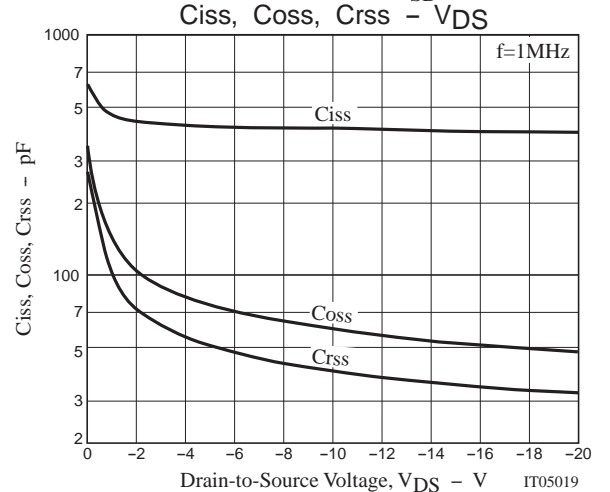
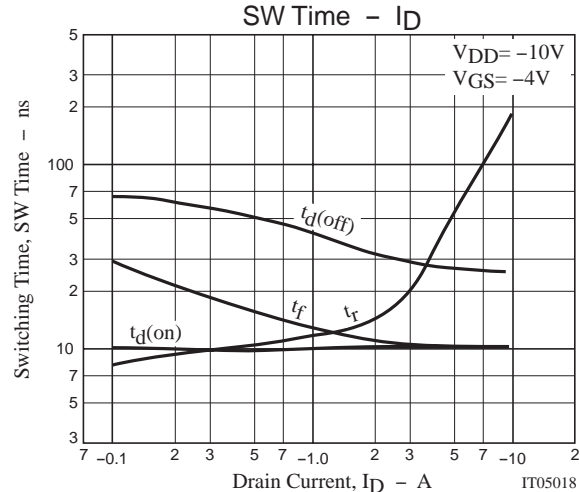
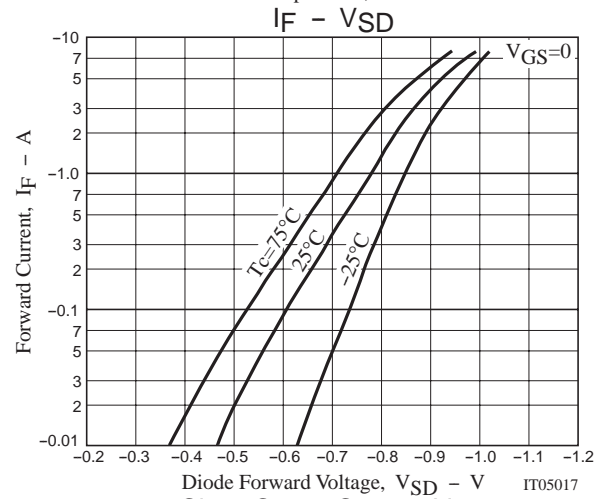
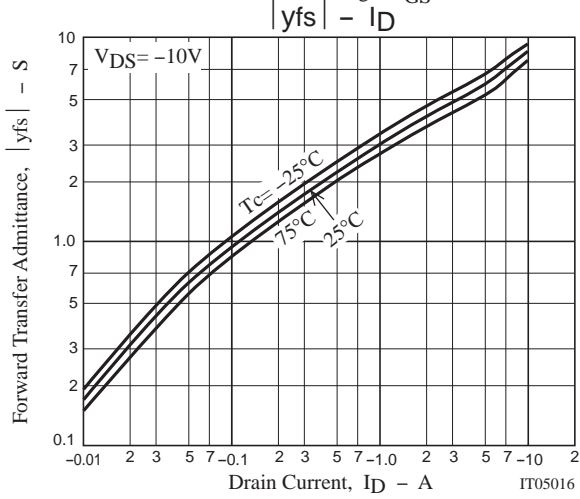
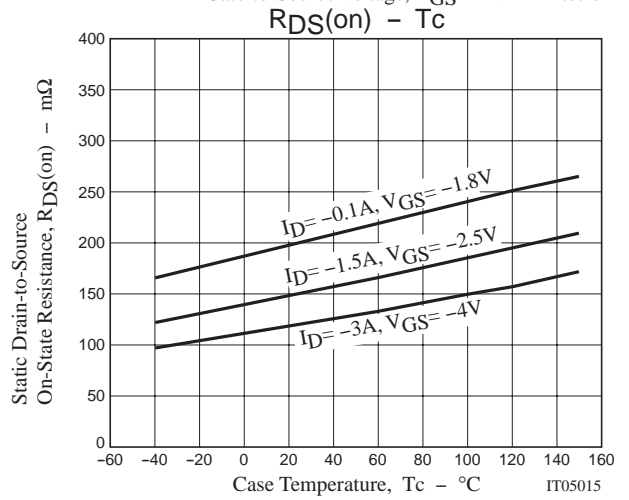
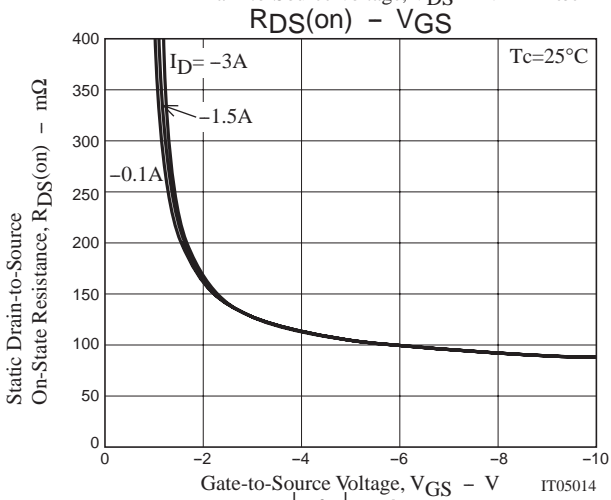
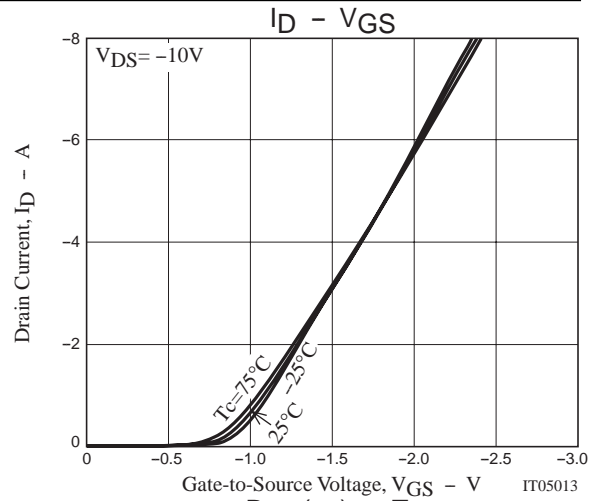
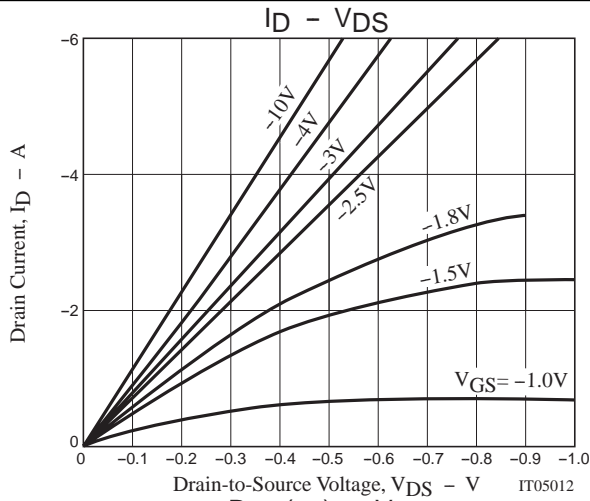
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =-1mA, V _{GS} =0	-20			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0			-10	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-0.3		-1.0	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-3A	2.1	3		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-3A, V _{GS} =-4V		120	160	mΩ
	R _{DS(on)2}	I _D =-1.5A, V _{GS} =-2.5V		150	210	mΩ
	R _{DS(on)3}	I _D =-0.1A, V _{GS} =-1.8V		200	300	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		410		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		60		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		40		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		20		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		30		ns
Fall Time	t _f	See specified Test Circuit.		10		ns
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4V, I _D =-6A		4.4		nC
Gate-to-Source Charge	Q _{gs}	V _{DS} =-10V, V _{GS} =-4V, I _D =-6A		0.6		nC
Gate-to-Drain "Miller" Charge	Q _{gd}	V _{DS} =-10V, V _{GS} =-4V, I _D =-6A		1.2		nC
Diode Forward Voltage	V _{SD}	I _S =-6A, V _{GS} =0	-1.0	-1.2		V

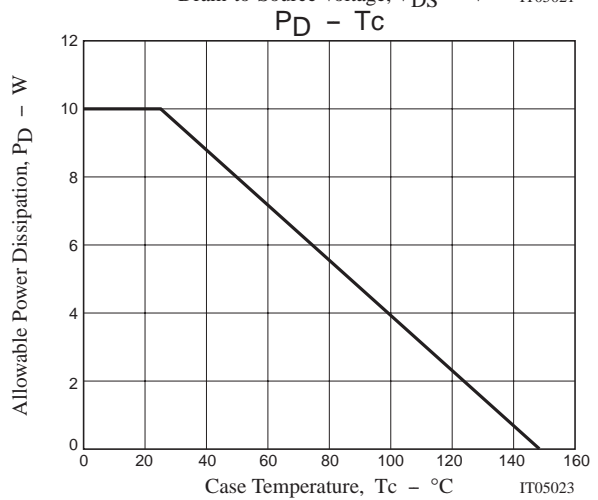
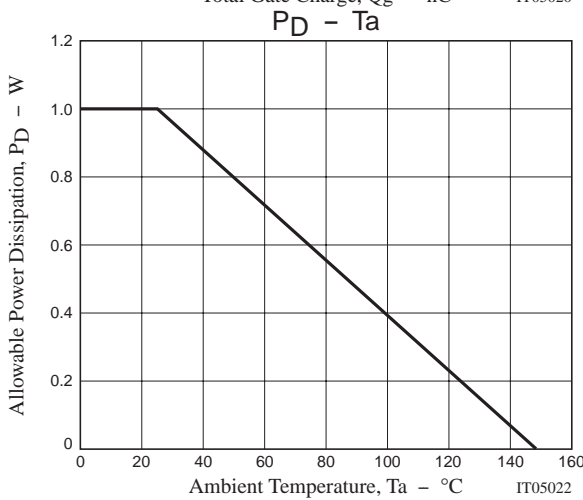
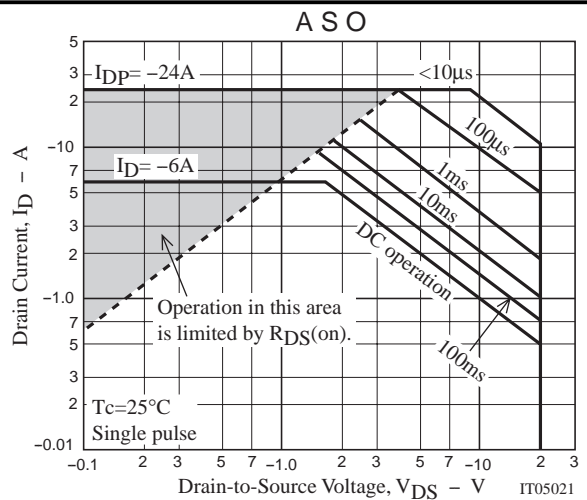
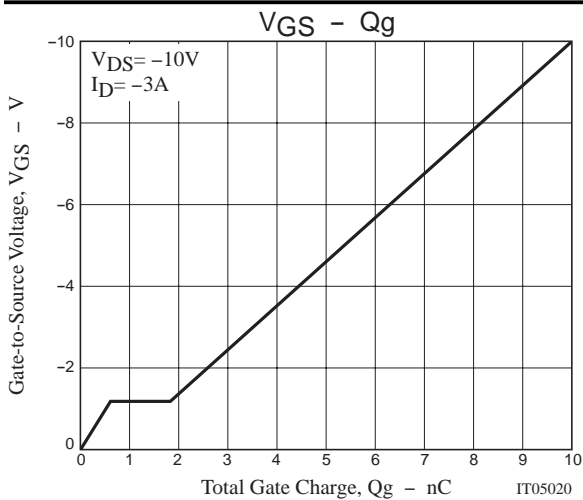
Marking : J643

Switching Time Test Circuit



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